MSC80213

NPN RF TRANSISTOR

DESCRIPTION:

The **ASI MSC80213** is a Silicon NPN Microwave Transistor Supplied in a Common Base Package, Designed for general purpose Applications up to 2.3 GHz.

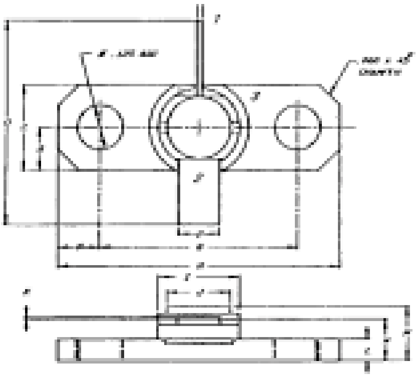
FEATURES:

- Hermetically Sealed Package
- Gold Metallization

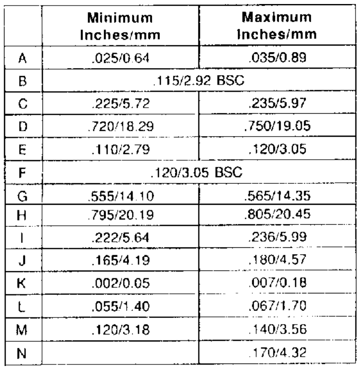
MAXIMUM RATINGS

I_C	600 mA
V_{CC}	26 V
V_{EB}	3.5 V
P_{DISS}	11.5 W @ T_C = 50 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	13 ^{O}C/W

PACKAGE 230 2L FLG



1 = Collector 2 = Emitter
3 = Base



	Minimum Inches/mm	Maximum Inches/mm
A	.025/0.64	.035/0.89
B	.115/2.92 BSC	
C	.225/5.72	.235/5.97
D	.720/18.29	.750/19.05
E	.110/2.79	.120/3.05
F	.120/3.05 BSC	
G	.555/14.10	.565/14.35
H	.795/20.19	.805/20.45
I	.222/5.64	.236/5.99
J	.165/4.19	.180/4.57
K	.002/0.05	.007/0.18
L	.055/1.40	.067/1.70
M	.120/3.18	.140/3.56
N		.170/4.32

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	I_C = 5.0 mA R_{BE} = 10Ω	44			V
BV_{CBO}	I_C = 1.0 mA	44			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CBO}	V_{CB} = 22 V			0.5	mA
h_{FE}	V_{CE} = 5.0 V I_C = 250 mA	30		300	
C_{OB}	V_{CB} = 22 V f = 1.0 MHz			5.0	pF
P_{out} P_G η_C	V_{CC} = 22 V P_{IN} = 0.38 W f = 2.3 GHz	3.8 10 40			W Db %